

Francois Silva

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

547
citations

1307594

7
h-index

1474206

9
g-index

10
all docs

10
docs citations

10
times ranked

513
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Detection of stable positive fixed charges in AlO _x activated during annealing with in situ modulated PhotoLuminescence. Solar Energy Materials and Solar Cells, 2021, 230, 111172. | 6.2 | 5 |
| 2 | Deleterious electrostatic interaction in silicon passivation stack between thin ALD Al ₂ O ₃ and its a-SiN _x :H capping layer: numerical and experimental evidences. Energy Procedia, 2017, 124, 91-98. | 1.8 | 3 |
| 3 | Ultrafast Deposition of Diamond by Plasma-Enhanced CVD. , 2014, , 217-268. | | 7 |
| 4 | Growth of large size diamond single crystals by plasma assisted chemical vapour deposition: Recent achievements and remaining challenges. Comptes Rendus Physique, 2013, 14, 169-184. | 0.9 | 133 |
| 5 | Growth strategy for controlling dislocation densities and crystal morphologies of single crystal diamond by using pyramidal-shape substrates. Diamond and Related Materials, 2013, 33, 71-77. | 3.9 | 34 |
| 6 | Effect of argon addition on the growth of thick single crystal diamond by high-power plasma CVD. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 2028-2032. | 1.8 | 28 |
| 7 | Defect analysis and excitons diffusion in undoped homoepitaxial diamond films after polishing and oxygen plasma etching. Diamond and Related Materials, 2009, 18, 1205-1210. | 3.9 | 45 |
| 8 | Dislocation imaging for electronics application crystal selection. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 4298-4304. | 1.8 | 29 |
| 9 | The control of growth parameters in the synthesis of high-quality single crystalline diamond by CVD. Journal of Crystal Growth, 2005, 284, 396-405. | 1.5 | 95 |
| 10 | CVD diamond films: from growth to applications. Current Applied Physics, 2001, 1, 479-496. | 2.4 | 168 |